# N-Channel 100-V (D-S) MOSFET

### **Key Features:**

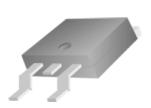
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

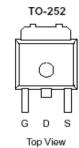
## **Typical Applications:**

- · LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)		
100	6 @ V <sub>GS</sub> = 10V	75		
	9 @ V <sub>GS</sub> = 6.5V	61		







ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			100	V		
Gate-Source Voltage		$V_{GS}$	±20	V		
Continuous Drain Current a	T <sub>C</sub> =25°C	I <sub>D</sub>	75			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	300	А		
Continuous Source Current (Diode Conduction) a	T <sub>C</sub> =25°C	I <sub>S</sub>	75	Α		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_D$	50	W		
Operating Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	3	C/VV		

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#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

### **Electrical Characteristics**

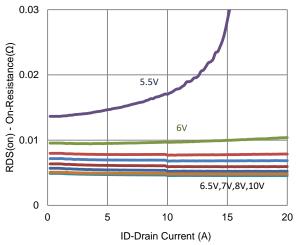
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lass	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA uA	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	100			Α	
Dunin Course On Besistance a	r	$V_{GS} = 10 \text{ V}, I_D = 38 \text{ A}$			6	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 6.5 \text{ V}, I_D = 30 \text{ A}$			9		
Forward Transconductance a	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 38 \text{ A}$		57		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 38 A, V <sub>GS</sub> = 0 V		0.89		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 6.5 \text{ V},$		27		nC	
Gate-Source Charge	$Q_gs$	$V_{DS} = 30 \text{ V}, V_{GS} = 0.3 \text{ V},$ $I_{D} = 20 \text{ A}$		15			
Gate-Drain Charge	$Q_gd$	1 <sub>D</sub> = 23 / X		9.7			
Turn-On Delay Time	$t_{d(on)}$	V 50 V D = 2.5 O		25			
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_{L} = 2.5 \Omega,$ $I_{D} = 20 \text{ A},$		21		no	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		42		ns	
Fall Time	t <sub>f</sub>	VGEN = 10 V, NGEN 0 12		70			
Input Capacitance	$C_{iss}$			2731			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		545		pF	
Reverse Transfer Capacitance	$C_{rss}$			436			

#### Notes

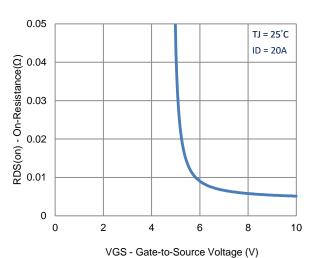
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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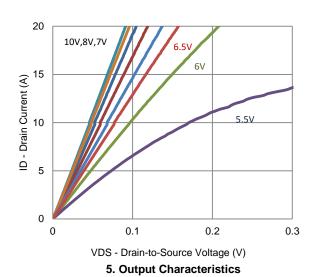
## **Typical Electrical Characteristics**

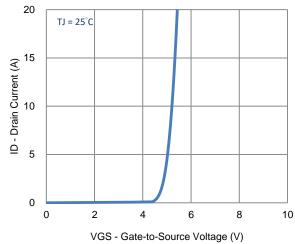


#### 1. On-Resistance vs. Drain Current

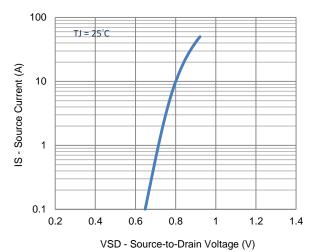


3. On-Resistance vs. Gate-to-Source Voltage

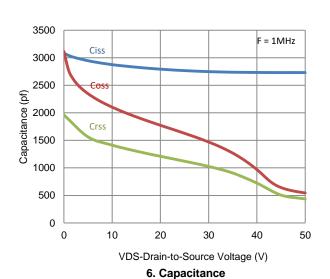




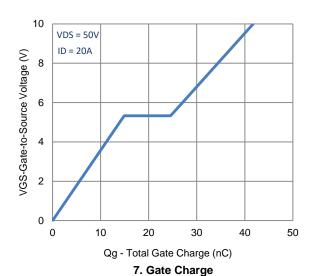
2. Transfer Characteristics

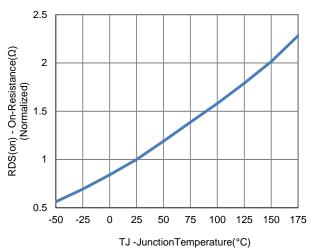


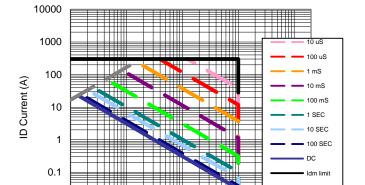
4. Drain-to-Source Forward Voltage



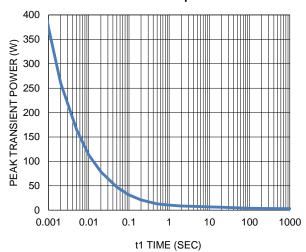
## **Typical Electrical Characteristics**







8. Normalized On-Resistance Vs Junction Temperature



VDS Drain to Source Voltage (V)

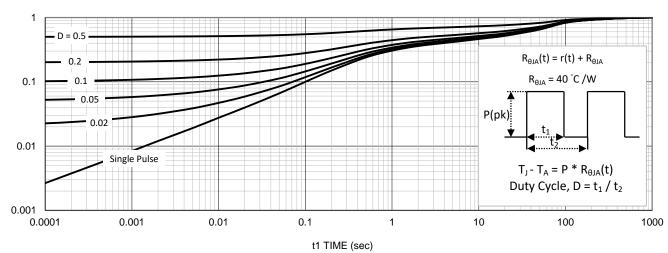
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9. Safe Operating Area

100

1000

10. Single Pulse Maximum Power Dissipation



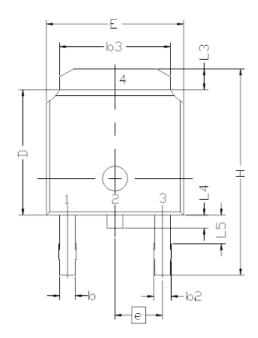
11. Normalized Thermal Transient Junction to Ambient

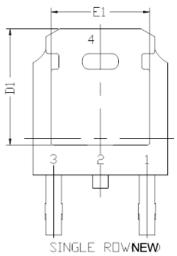
0.01

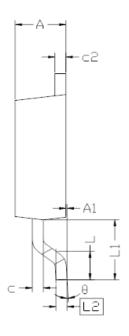
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# **Package Information**







CVADDI	DIMENS:	[DNAL	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2	.743 R	ĖF
L2	0.	.508 BS	
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5,21	5.34	5.46
е	2.	286 BS	
Α	2,20	2,30	2,38
A1	0		0.127
_	0.45	0.50	0.60
c2	0.45	0,50	0.58
D1	5.30		
E1	4.40		
θ	0°		10°

### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.